



UF630

Power MOSFET

200V, 9A N-CHANNEL POWER MOSFET

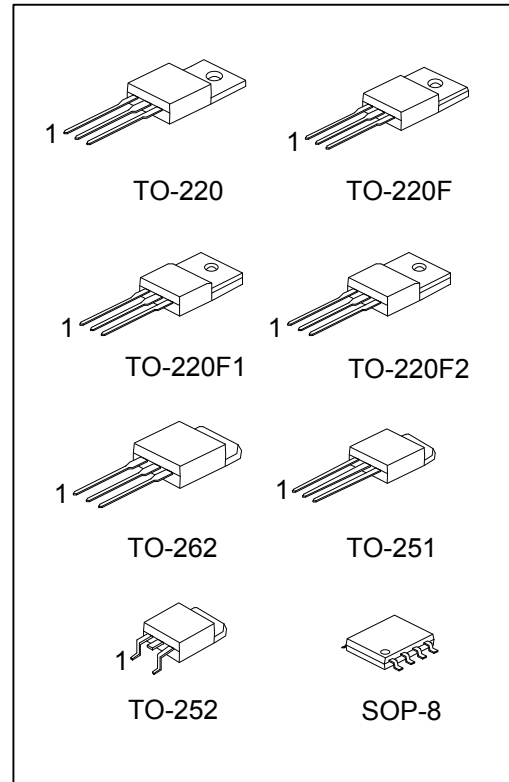
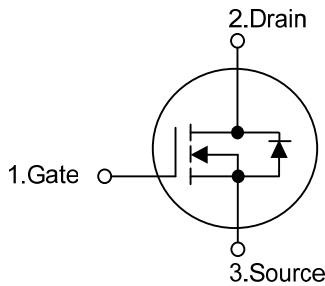
DESCRIPTION

The N-Channel enhancement mode silicon gate power MOSFET is designed for high voltage, high speed power switching applications such as switching regulators, switching converters, solenoid, motor drivers, relay drivers.

FEATURES

- * $R_{DS(ON)} < 0.4\Omega @ V_{GS} = 10V, I_D = 5A$
- * Ultra Low Gate Charge (typical 19 nC)
- * Low Reverse Transfer Capacitance ($C_{RSS} = \text{typical } 80 \text{ pF}$)
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability

SYMBOL



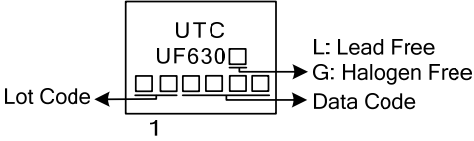
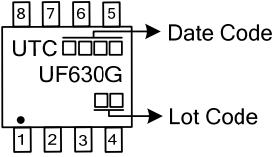
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
UF630L-TA3-T	UF630G-TA3-T	TO-220	G	D	S	-	-	-	-	-	Tube
UF630L-TF1-T	UF630G-TF1-T	TO-220F1	G	D	S	-	-	-	-	-	Tube
UF630L-TF2-T	UF630G-TF2-T	TO-220F2	G	D	S	-	-	-	-	-	Tube
UF630L-TF3-T	UF630G-TF3-T	TO-220F	G	D	S	-	-	-	-	-	Tube
UF630L-TM3-T	UF630G-TM3-T	TO-251	G	D	S	-	-	-	-	-	Tube
UF630L-TN3-R	UF630G-TN3-R	TO-252	G	D	S	-	-	-	-	-	Tape Reel
UF630L-T2Q-T	UF630G-T2Q-T	TO-262	G	D	S	-	-	-	-	-	Tube
-	UF630G-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>UF630L-TA3-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F, TM3: TO-251, TN3: TO-252, T2Q: TO-262, S08: SOP-8</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p>
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■ MARKING

TO-220 / TO-220F / TO-220F1 TO-220F2 / TO-252 / TO-262	SOP-8
 <p>UTC UF630</p> <p>Lot Code</p> <p>1</p> <p>L: Lead Free G: Halogen Free Data Code</p>	 <p>UTC UF630G</p> <p>Date Code</p> <p>Lot Code</p>

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	200	V
Drain-Gate Voltage ($R_{GS} = 20\text{k}\Omega$, $T_J = 25^\circ\text{C} \sim 125^\circ\text{C}$)		V_{DGR}	200	V
Gate-Source Voltage		V_{GSS}	± 20	V
Continuous Drain Current		I_D	9	A
Pulsed Drain Current (Note 2)		I_{DM}	36	A
Single Pulse Avalanche Energy (Note 3)		E_{AS}	150	mJ
Power Dissipation	TO-220/TO-262	P_D	73	W
	TO-220F1/ TO-220F		38	
	TO-220F2		42	
	TO-251/ TO-252		46	
	SOP-8		5	
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J .

3. $L = 4\text{mH}$, $I_{AS} = 8.3\text{A}$, $V_{DD} = 20\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-262	θ_{JA}	62.5	$^\circ\text{C/W}$
	TO-220F1/ TO-220F			
	TO-220F2			
	TO-251/ TO-252			
	SOP-8			
Junction to Case	TO-220/TO-262	θ_{JC}	1.71	$^\circ\text{C/W}$
	TO-220F1/ TO-220F		3.31	
	TO-220F2		2.98	
	TO-251/ TO-252		2.7	
	SOP-8		24	

■ ELECTRICAL SPECIFICATIONS (T_C=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA	200			V
On-State Drain Current (Note 1)	I _{D(ON)}	V _{DS} > I _{D(ON)} × R _{DS(ON)MAX} , V _{GS} = 10V	9			A
Drain-Source Leakage Current	I _{DSS}	V _{DS} = Rated BV _{DSS} , V _{GS} = 0V			10	μA
Gate-Source Leakage Current	Forward	V _{GS} = 20V, V _{DS} = 0V V _{GS} = -20V, V _{DS} = 0V			100	nA
	Reverse				-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250μA	2		4	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 5A		0.25	0.4	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz		600		pF
Output Capacitance	C _{OSS}			250		pF
Reverse Transfer Capacitance	C _{RSS}			80		pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	V _{DD} = 90V, I _D ≈ 9A, R _{GS} = 9.1Ω, V _{GS} = 10V, R _L = 9.6Ω (Note 1, 2)			30	ns
Turn-On Rise Time	t _R				50	ns
Turn-Off Delay Time	t _{D(OFF)}				50	ns
Turn-Off Fall Time	t _F				40	ns
Total Gate Charge	Q _G		V _{GS} = 10V, I _D = 9A, V _{DS} = 0.8 × Rated BV _{DSS}		19	30
Gate-Source Charge	Q _{GS}	I _{G(REF)} = 1.5mA		10		nC
Gate-Drain Charge	Q _{GD}			9		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0V, I _S = 9.0A			2	V
Maximum Continuous Drain-Source Diode Forward Current	I _S				9	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				36	A
Reverse Recovery Time	t _{rr}	I _S = 9.0A, di _S /dt = 100A/μs		450		ns
Reverse Recovery Charge	Q _{RR}	(Note 1)		3		μC

Notes: 1. Pulse Test: Pulse width ≤300μs, Duty cycle ≤2%.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

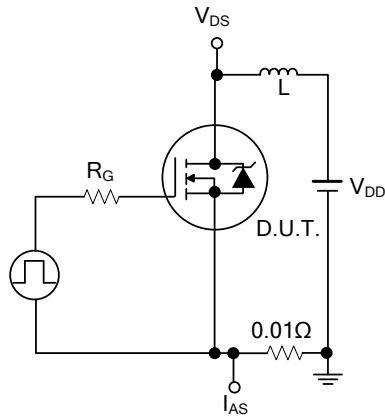


Fig.1. Unclamped Energy Test Circuit

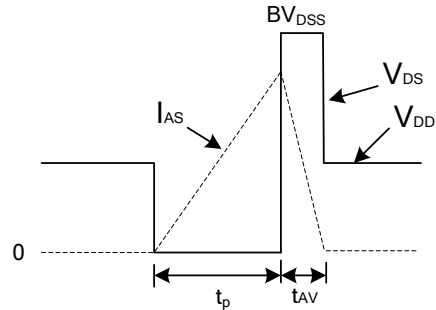


Fig.2 Unclamped Energy Waveforms

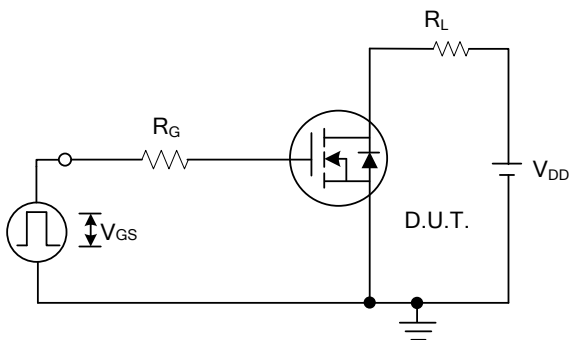


Fig.3 Switching Time Test Circuit

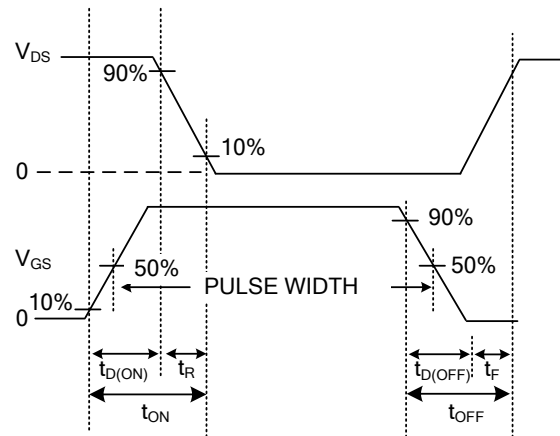


Fig.4 Resistive Switching Waveforms

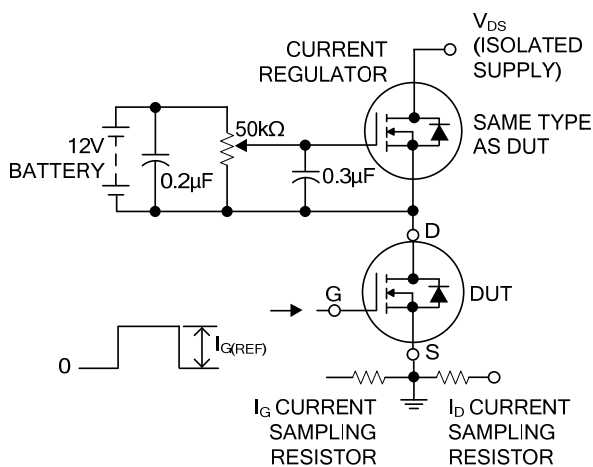


Fig.5 Gate Charge Test Circuit

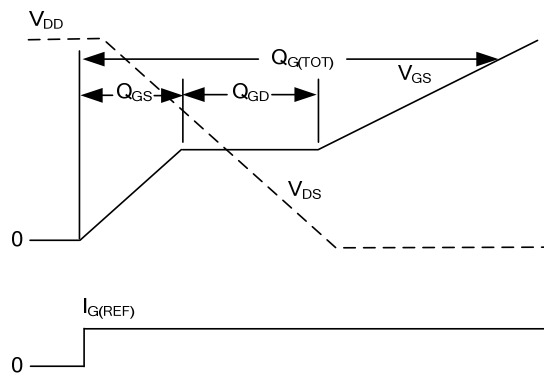
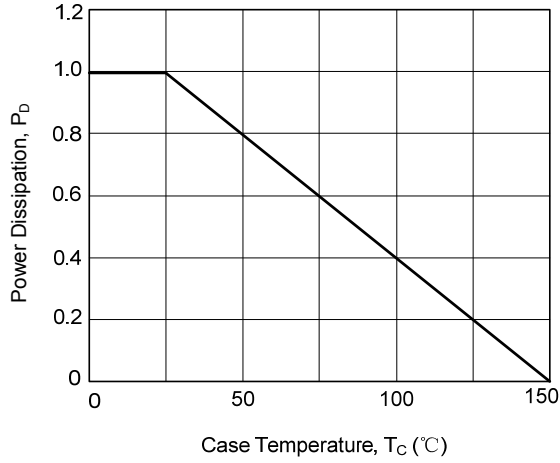


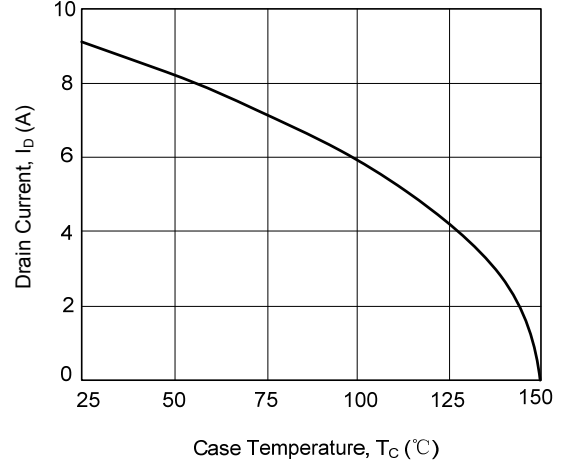
Fig.6 Gate Charge Waveforms

TYPICAL CHARACTERISTICS

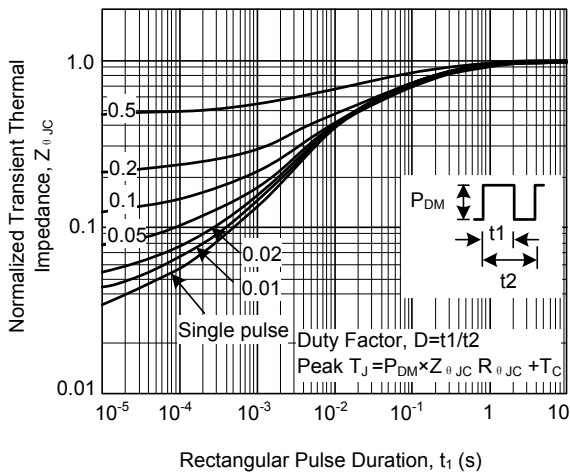
Normalized Power Dissipation vs. Case Temperature



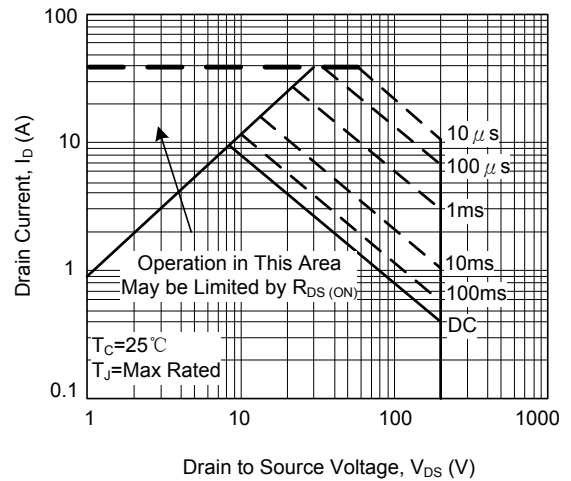
Maximum Continuous Drain Current vs. Case Temperature



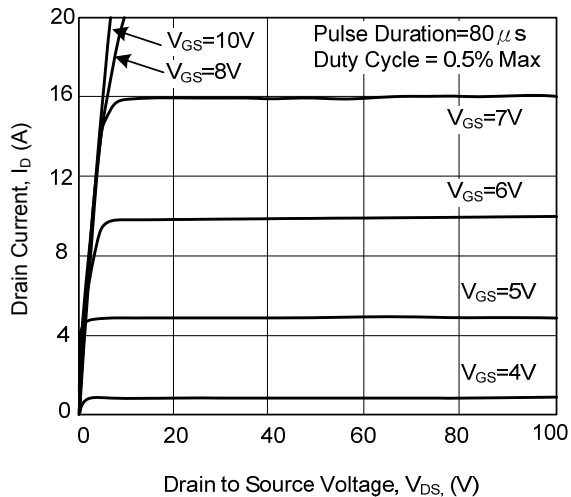
Normalized Transient Thermal Impedance



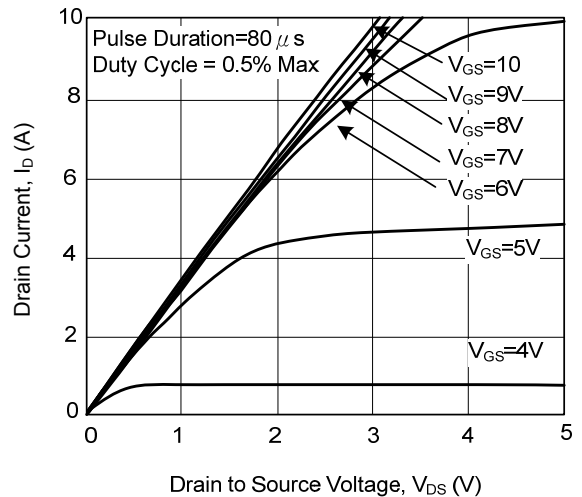
Forward Bias Safe Operating Area



Output Characteristics

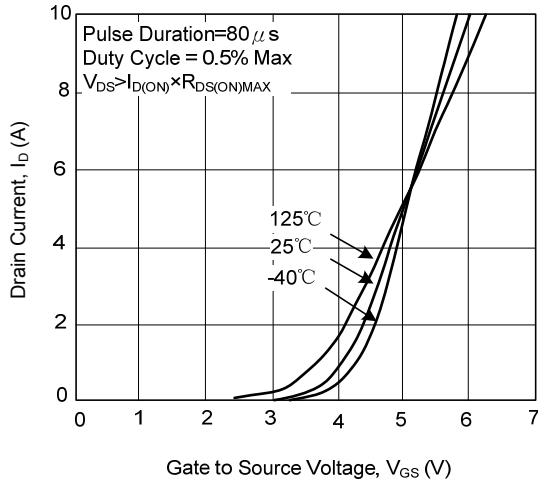


Saturation Characteristics

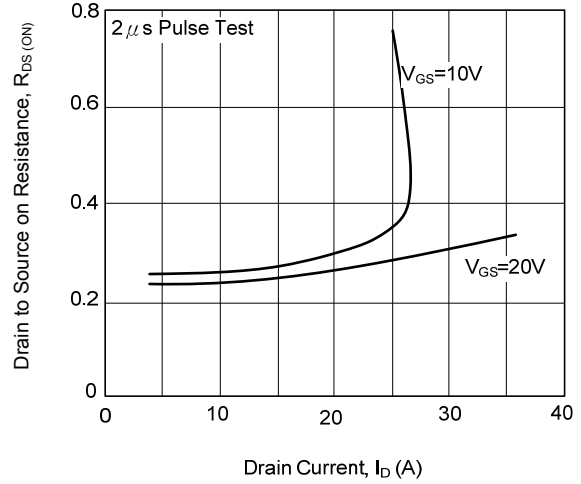


■ TYPICAL CHARACTERISTICS (Cont.)

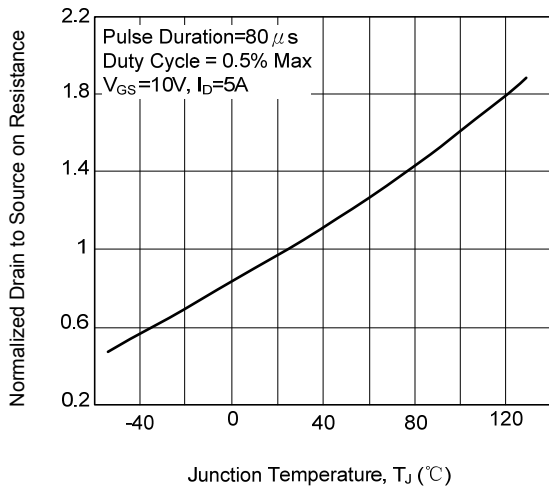
Transfer Characteristics



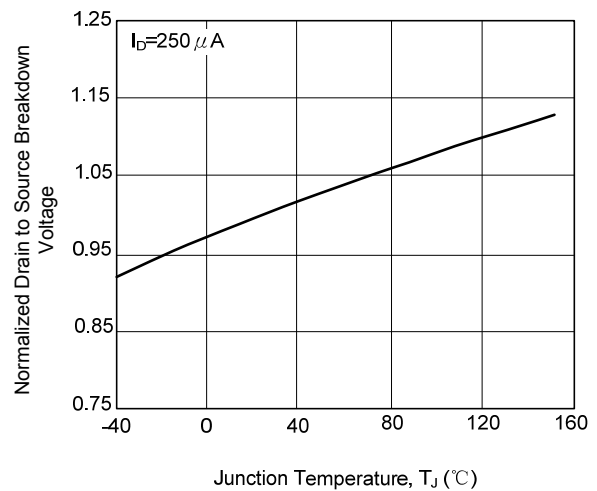
Drain to Source on Resistance vs. Gate Voltage and Drain Current



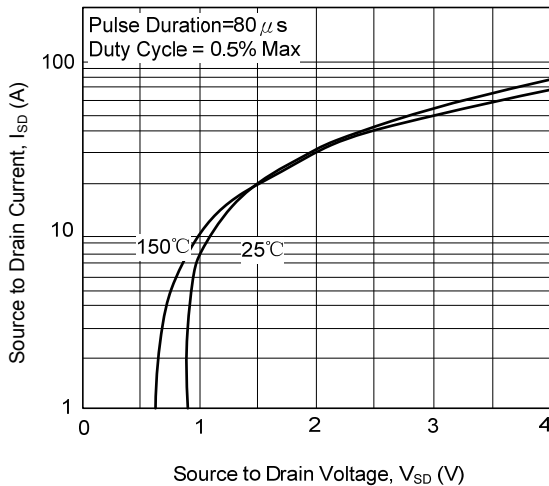
Normalized Drain to Source on Resistance vs. Junction Temperature



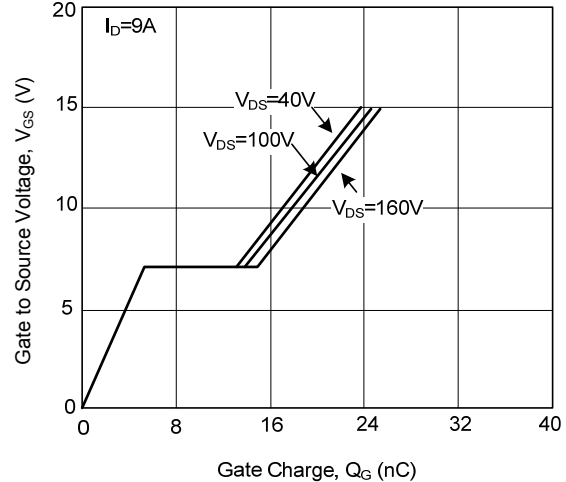
Normalized Drain to Source Breakdown Voltage vs. Junction Temperature



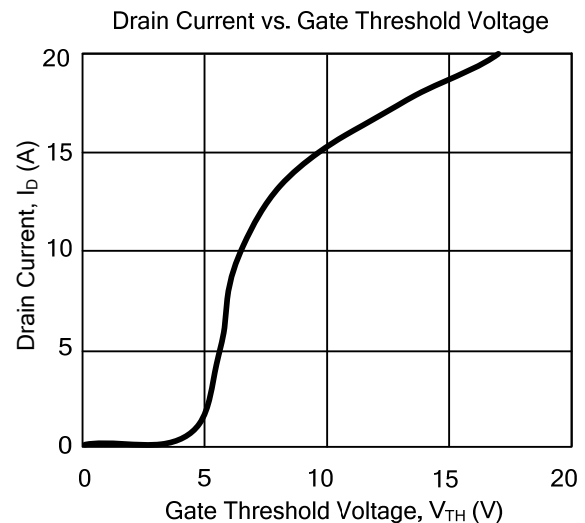
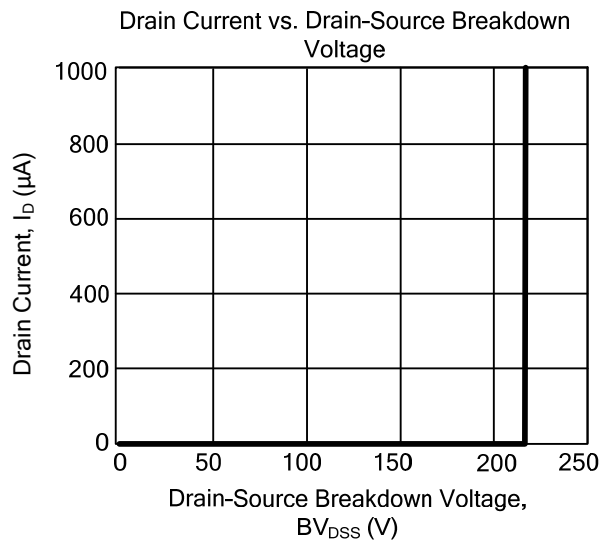
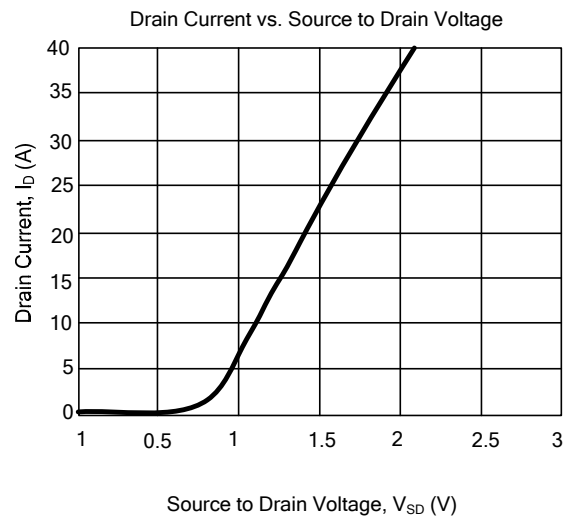
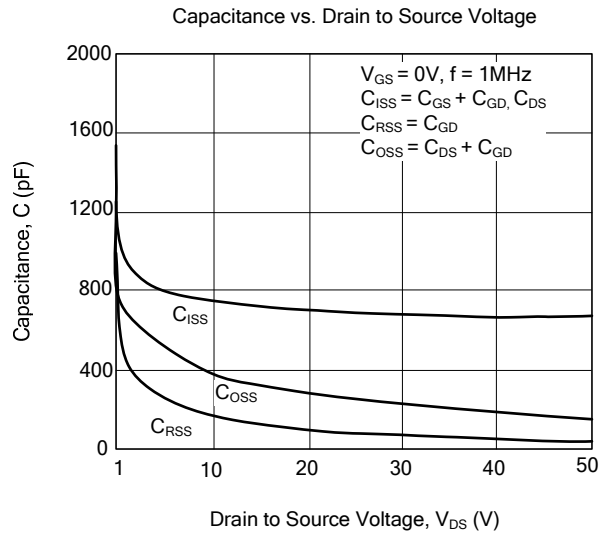
Source to Drain Diode Voltage



Gate to Source Voltage vs. Gate Charge



■ TYPICAL CHARACTERISTICS (Cont.)



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